

**AMENDMENTS TO THE CLAIMS**

Claims 1 to 23 (Canceled)

24. (Withdrawn) A phosphor of SiC excited by an external light source for emitting light, doped with N and at least one of B and Al.

25. (Withdrawn) The phosphor of Sic according to claim 24, wherein both of the doping concentration with at least one of B and Al and the doping concentration with N are  $10^{15}/\text{cm}^3$  to  $10^{20}/\text{cm}^3$ .

26. (Withdrawn) The phosphor of SiC according to claim 25, wherein both of the doping concentration with at least one of B and Al and the doping concentration with N are  $10^{16}/\text{cm}^3$  to  $10^{20}/\text{cm}^3$ .

27. (Withdrawn) The phosphor of SiC according to claim 24, emitting fluorescence having a wavelength of 500 nm to 750 nm with a peak wavelength in the range of 500 nm to 650 nm.

28. (Withdrawn) The phosphor of SiC according to claim 27, wherein SiC is doped with N and B, the concentration of either N or B is  $10^{15}/\text{cm}^3$  to  $10^{18}/\text{cm}^3$ , and the concentration of either B or N is  $10^{16}/\text{cm}^3$  to  $10^{19}/\text{cm}^3$ .

29. (Withdrawn) The phosphor of SiC according to claim 24, emitting fluorescence having a wavelength of 400 nm to 750 nm with a peak wavelength in the range of 400 nm to 550 nm.

30. (Withdrawn) The phosphor of SiC according to claim 29, wherein SiC is doped with N and Al, the concentration of either N or Al is  $10^{15}/\text{cm}^3$  to  $10^{18}/\text{cm}^3$ , and the concentration of either Al or N is  $10^{16}/\text{cm}^3$  to  $10^{19}/\text{cm}^3$ .

31. (Withdrawn) A method of manufacturing a phosphor of SiC excited by an external light source for emitting fluorescence having a wavelength of 500 nm to 750 nm with a peak wavelength in the range of 500 nm to 650 nm and doped with N and B so that the concentration of either N or B is  $10^{15}/\text{cm}^3$  to  $10^{18}/\text{cm}^3$  and the concentration of either B or N is  $10^{16}/\text{cm}^3$  to  $10^{19}/\text{cm}^3$ ,

by forming an SiC crystal by sublimation recrystallization with a B source of LaB<sub>6</sub>, B<sub>4</sub>C, TaB<sub>2</sub>, NbB<sub>2</sub>, ZrB<sub>2</sub>, HfB<sub>2</sub>, BN or carbon containing B.

32. (Withdrawn) The method of manufacturing a phosphor of SiC according to claim 31, performing thermal annealing at a temperature of at least 1300°C for at least one hour after sublimation recrystallization or thermal diffusion.

33. (Withdrawn) A method of manufacturing a phosphor of SiC excited by an external light source for emitting fluorescence having a wavelength of 500 nm to 750 nm with a peak wavelength in the range of 500 nm to 650 nm and doped with N and B so that the concentration of either N or B is  $10^{15}/\text{cm}^3$  to  $10^{18}/\text{cm}^3$  and the concentration of either B or N is  $10^{16}/\text{cm}^3$  to  $10^{19}/\text{cm}^3$ ,

by thermally diffusing a B source of simple B, LaB<sub>6</sub>, B<sub>4</sub>C, TaB<sub>2</sub>, NbB<sub>2</sub>, ZrB<sub>2</sub>, HfB<sub>2</sub> or BN into SiC under a vacuum or an inert gas atmosphere at a temperature of at least 1500°C.

34. (Withdrawn) The method of manufacturing a phosphor of SiC according to claim 33, performing thermal annealing at a temperature of at least 1300°C for at least one hour after sublimation recrystallization or thermal diffusion.

35. (Withdrawn) The method of manufacturing a phosphor of SiC according to claim 33, removing a surface layer after thermal diffusion.

36. (Withdrawn) A substrate for a semiconductor consisting of a 6H-SiC single-crystalline phosphor excited by an external light source for emitting light and doped with N and at least one of B and Al.

37. (Withdrawn) The substrate for a semiconductor according to claim 36, consisting of a 6H-SiC single-crystalline phosphor doped with N and B for emitting fluorescence having a wavelength of 500 nm to 750 nm with a peak wavelength in the range of 500 nm to 650 nm.

38. (Withdrawn) The substrate for a semiconductor according to claim 36, consisting of a 6H-SiC single-crystalline phosphor doped with N and Al for emitting fluorescence having a wavelength of 400 nm to 750 nm with a peak wavelength in the range of 400 nm to 550 nm.

39. (Withdrawn) A method of manufacturing a substrate for a semiconductor consisting of a 6H-SiC single-crystalline phosphor excited by an external light source for emitting fluorescence having a wavelength of 500 nm to 750 nm with a peak wavelength in the range of 500 nm to 650 nm and doped with N and B so that the concentration of either N or B is  $10^{15}/\text{cm}^3$  to  $10^{18}/\text{cm}^3$  and the concentration of either B or N is  $10^{16}/\text{cm}^3$  to  $10^{19}/\text{cm}^3$ , comprising the steps of:

thermally diffusing a B source of simple B, LaB<sub>6</sub>, B<sub>4</sub>C, TaB<sub>2</sub>, NbB<sub>2</sub>, ZrB<sub>2</sub>, HfB<sub>2</sub> or BN into SiC under a vacuum or an inert gas atmosphere at a temperature of at least 1500°C; and  
removing a surface layer.

40. (Withdrawn) The method of manufacturing a substrate for a semiconductor according to claim 39, performing thermal annealing at a temperature of at least 1300°C after sublimation recrystallization or thermal diffusion.

41. (Withdrawn) A method of manufacturing a substrate for a semiconductor consisting of a 6H-SiC single-crystalline phosphor excited by an external light source for emitting fluorescence having a wavelength of 500 nm to 750 nm with a peak wavelength in the range of 500 nm to 650 nm and doped with N and B so that the concentration of either N or B is  $10^{15}/\text{cm}^3$  to  $10^{18}/\text{cm}^3$  and the concentration of either B or N is  $10^{16}/\text{cm}^3$  to  $10^{19}/\text{cm}^3$ , wherein

atmosphere gas in crystal growth contains N<sub>2</sub> gas of 1 % to 30 % in gas partial pressure, and raw material SiC contains 0.05 mol % to 15 mol % of a B source, and an SiC crystal is formed by sublimation recrystallization.

42. (Withdrawn) The method of manufacturing a substrate for a semiconductor according to claim 41, performing thermal annealing at a temperature of at least 1300°C after sublimation recrystallization or thermal diffusion.

43. (Withdrawn) Powder for a semiconductor consisting of a 6H-SiC single-crystalline phosphor excited by an external light source for emitting fluorescence having a wavelength of 500 nm to 750 nm with a peak wavelength in the range of 500 nm to 650 nm, having a particle diameter of 2 µm to 10 µm and a central particle diameter of 3 µm to 6 µm.

**44 - 47. (Canceled)**

48. (Previously Presented) A light-emitting apparatus having one or at least two layers consisting of a 6H-SiC single-crystalline phosphor doped with N and at least one of B and Al on a substrate of SiC for a semiconductor and comprising a light-emitting device of a nitride semiconductor on said 6H-SiC single-crystalline phosphor layer(s).

49. (Previously Presented) The light-emitting apparatus according to claim 48, wherein the emission wavelength of said light-emitting device of a nitride semiconductor is not more than 408 nm.

50. (Previously Presented) The light-emitting apparatus according to claim 48, wherein both of the doping concentration with at least one of B and Al and the doping concentration with N in said 6H-SiC single-crystalline phosphor are  $10^{16}/\text{cm}^3$  to  $10^{19}/\text{cm}^3$ .

51. (Previously Presented) The light-emitting apparatus according to claim 50, wherein both of the doping concentration with at least one of B and Al and the doping concentration with N in said 6H-SiC single-crystalline phosphor are  $10^{17}/\text{cm}^3$  to  $10^{19}/\text{cm}^3$ .

52. (New) A light-emitting apparatus according to claim 48, wherein  
the said 6H-SiC single-crystalline phosphor having a wavelength of 500 nm to 750 nm  
with a peak wavelength in the range of 500 nm to 650 nm.

53. (New) A light-emitting apparatus having a first SiC layer doped with Al and N on a  
substrate of SiC and a second SiC layer doped with B and N of the first SiC layer for a  
semiconductor and comprising a light-emitting device of a nitride semiconductor on said 6H-SiC  
single-crystalline phosphor layer(s).

54. (New) The light-emitting apparatus according to claim 53, wherein  
the emission wavelength of said light-emitting device of a nitride semiconductor is not  
more than 408 nm.

55. (New) The light-emitting apparatus according to claim 53, wherein  
both of the doping concentration with at least one of B and Al and the doping  
concentration with N in said 6H-SiC single-crystalline phosphor are  $10^{16}/\text{cm}^3$  to  $10^{19}/\text{cm}^3$ .

56. (New) The light-emitting apparatus according to claim 53, wherein  
both of the doping concentration with at least one of B and Al and the doping  
concentration with N in said 6H-SiC single-crystalline phosphor are  $10^{17}/\text{cm}^3$  to  $10^{19}/\text{cm}^3$ .

57. (New) The light-emitting apparatus according to claim 53, wherein  
the said 6H-SiC single-crystalline phosphor having a wavelength of 500 nm to 750 nm  
with a peak wavelength in the range of 500 nm to 650 nm.